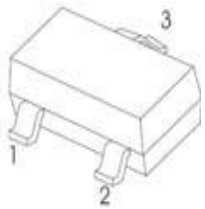
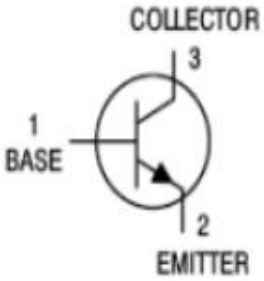
| TRANSI STOR (NPN) | SOT-23 Plastic-Encapsulate Transistors |
|---|---|

SOT-23




1.BASE
2.EMITTER
3.COLLECTOR

Marking :J3Y

## Features

※ Complimentary to S8550

※ Collector Current: Ic=0.5A

**MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)**

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Collector-Base Voltage | VCBO | 40 | V |
| Collector-Emitter Voltage | VCEO | 25 | V |
| Emitter-Base Voltage | VEBO | 5 | V |
| Collector Current | IC | 500 | mA |
| Collector Power Dissipation | PC | 300 | mW |
| Thermal Resistance From Junction To Ambient | RΘJA | 417 | ℃/W |
| Junction Temperature | Tj | 150 | ℃ |
| Storage Temperature | Tstg | -55～+150 | ℃ |

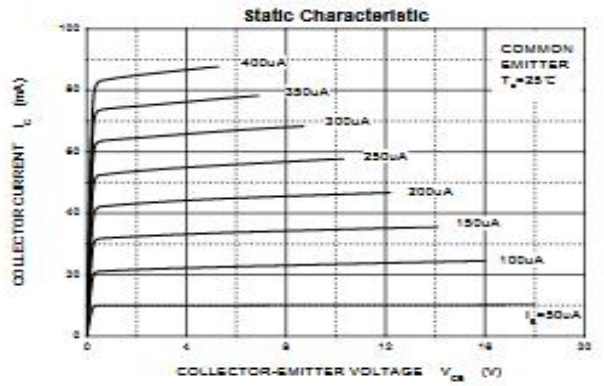
## ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

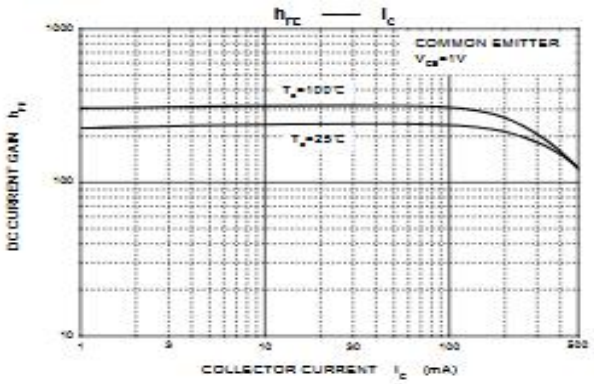
| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Collector-base breakdown voltage | V(BR)CBO | IC= 100μA, IE=0 | 40 | 126 | 200 | V |
| Collector-emitter breakdown voltage | V(BR)CEO | IC= 1mA, IB=0 | 25 | 50 | 100 | V |
| Emitter-base breakdown voltage | V(BR)EBO | IE= 100μA, IC=0 | 5 | 8 | 30 | V |
| Collector cut-off current | ICBO | VCB= 40 V , IE=0 | | | 0.1 | μA |
| Collector cut-off current | ICEO | VCB= 25V , IE=0 | | | 0.1 | μA |
| Emitter cut-off current | IEBO | VEB= 5V , IC=0 | | | 0.1 | μA |
| DC current gain | hFE | VCE=5V, IC= 50mA | 85 | | 400 | |
| | hFE | VCE=5V, IC= 500mA | 40 | | | |
| Collector-emitter saturation voltage | VCE(sat) | IC=500 mA, IB= 50mA | | | 0.5 | V |
| Base-emitter saturation voltage | VBE(sat) | IC=500 mA, IB= 50mA | | | 1.2 | V |
| Transition frequency | fT | VCE=6V, IC= 20mA f=30MHz | 150 | | | MHz |

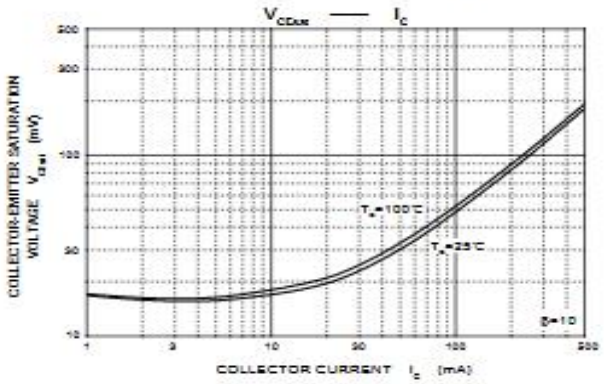
## CLASSIFICATION OF hFE

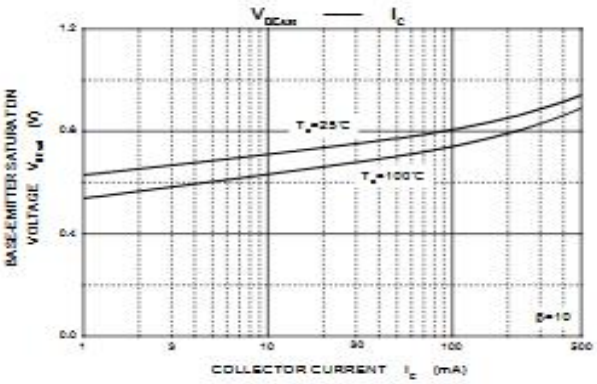
| Rank | L | H | J |
|---|---|---|---|
| Range | 120-200 | 200-350 | 300-400 |
| MARKING: | | J3Y | |

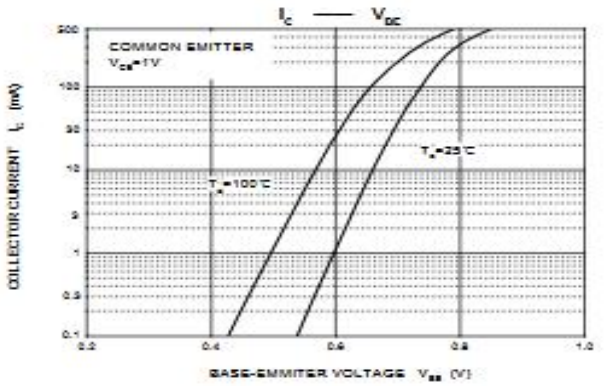
## TYPICAL ELEC TRICAL AND THERMAL CHARACTERISTICS

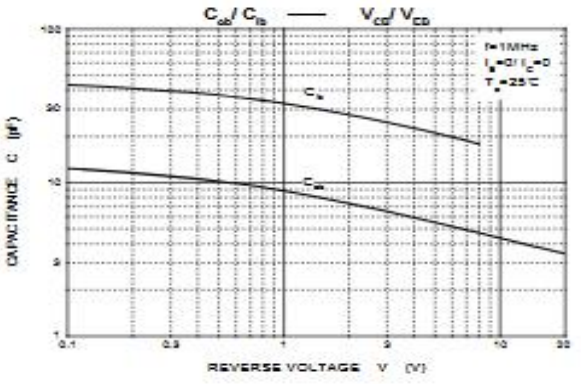


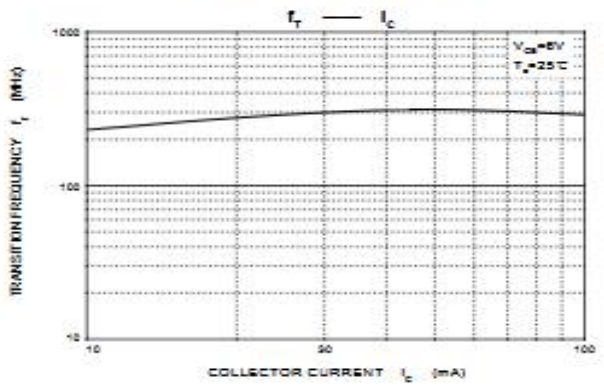



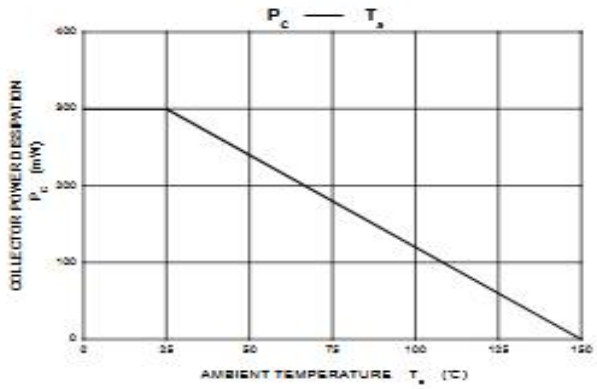



单击下面可查看定价，库存，交付和生命周期等信息

>>DIOS(迪恩思)